

# Rectifier diodes schottky barrier

## PBYR2525CT series

### GENERAL DESCRIPTION

Dual nickel silicide schottky barrier rectifier diodes in a plastic envelope featuring low forward voltage drop and absence of stored charge. These devices can withstand reverse voltage transients and have guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies with 3 V - 3.3 V outputs, or as or-ing diodes in fault tolerant power supply systems.

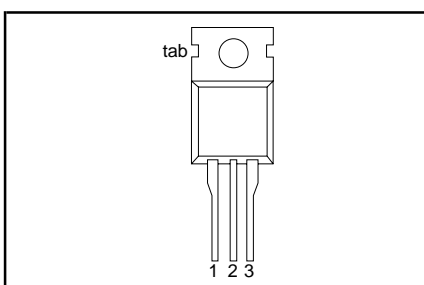
### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
$V_{RRM}$	Repetitive peak reverse voltage	<b>20CT</b> 20	<b>25CT</b> 25	V
$V_F$	Forward voltage	0.41	0.41	V
$I_{O(AV)}$	Average output current (both diodes conducting)	30	30	A

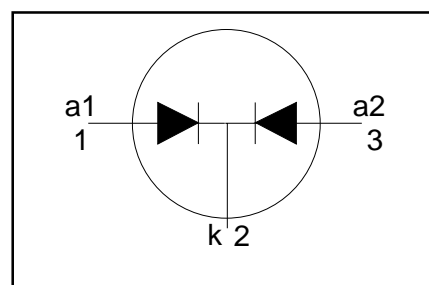
### PINNING - TO220AB

PIN	DESCRIPTION
1	anode 1 (a)
2	cathode (k)
3	anode 2 (a)
tab	cathode (k)

### PIN CONFIGURATION



### SYMBOL



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
$V_{RRM}$	Repetitive peak reverse voltage	$T_{mb} \leq 109\text{ }^{\circ}\text{C}$	-	<b>-20</b> 20	<b>-25</b> 25	V
$V_{RWM}$	Crest working reverse voltage		-	20	25	V
$V_R$	Continuous reverse voltage		-	20	25	V
$I_{O(AV)}$	Average output current (both diodes conducting)	square wave; $\delta = 0.5$ ; $T_{mb} \leq 135\text{ }^{\circ}\text{C}$	-	30		A
$I_{O(RMS)}$	RMS output current (both diodes conducting)		-	43		A
$I_{FRM}$	Repetitive peak forward current per diode	$t = 25\text{ }\mu\text{s}$ ; $\delta = 0.5$ ; $T_{mb} \leq 135\text{ }^{\circ}\text{C}$	-	30		A
$I_{FSM}$	Non-repetitive peak forward current, per diode	$t = 10\text{ ms}$	-	180		A
		$t = 8.3\text{ ms}$ sinusoidal $T_j = 125\text{ }^{\circ}\text{C}$ prior to surge; with reapplied $V_{RRM(max)}$	-	200		A
$I^2t$	$I^2t$ for fusing	$t = 10\text{ ms}$	-	162		A <sup>2</sup> s
$I_{RRM}$	Repetitive peak reverse current per diode	$t_p = 2\text{ }\mu\text{s}$ ; $\delta = 0.001$	-	2		A
$I_{RSM}$	Non-repetitive peak reverse current per diode	$t_p = 100\text{ }\mu\text{s}$	-	2		A
$T_{stg}$	Storage temperature		-65	175		$^{\circ}\text{C}$
$T_j$	Operating junction temperature		-	150		$^{\circ}\text{C}$

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	per diode	-	-	1.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	both diodes in free air	-	-	1.0	K/W
			-	60	-	K/W

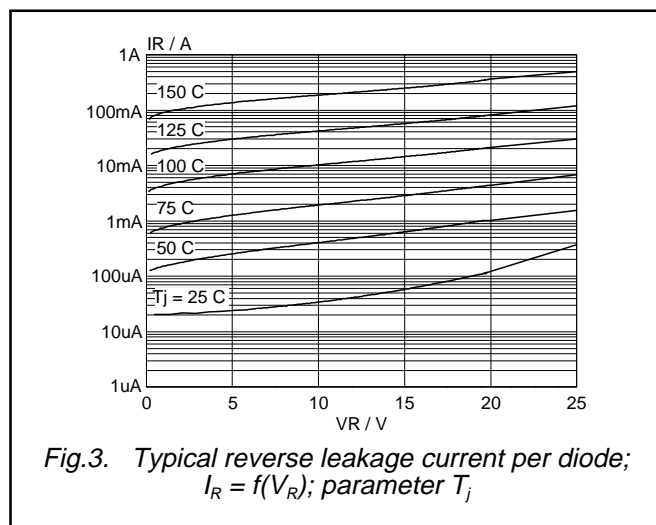
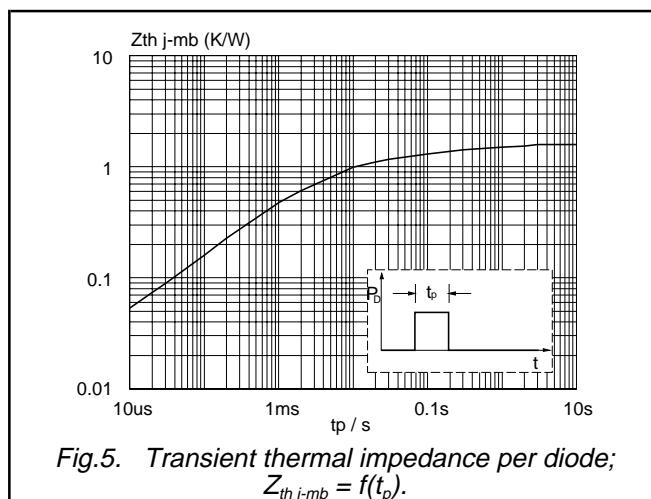
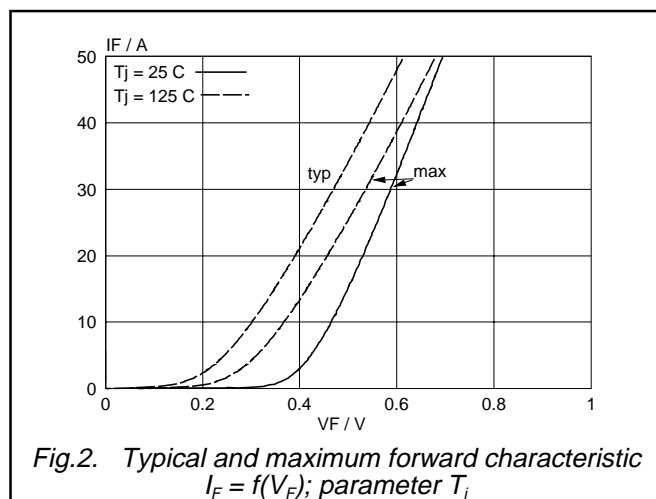
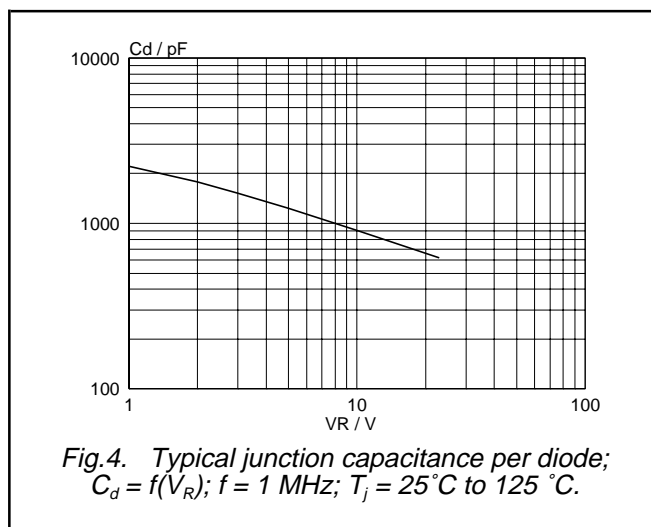
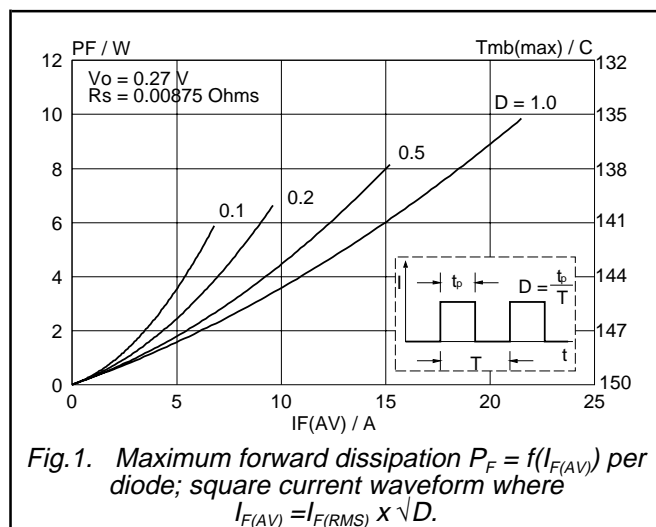
### STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_F$	Forward voltage (per diode)	$I_F = 15\text{ A}; T_j = 125\text{ °C}$	-	0.33	0.41	V
		$I_F = 30\text{ A}; T_j = 125\text{ °C}$	-	0.43	0.50	V
		$I_F = 30\text{ A}$	-	0.51	0.60	V
$I_R$	Reverse current (per diode)	$V_R = V_{RRM}$	-	2.0	10	mA
		$V_R = V_{RRM}; T_j = 100\text{ °C}$	-	30	80	mA
$C_d$	Junction capacitance (per diode)	$f = 1\text{ MHz}; V_R = 5\text{ V}; T_j = 25\text{ °C to }125\text{ °C}$	-	900	-	pF

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### MECHANICAL DATA

*Dimensions in mm*

*Net Mass: 2 g*

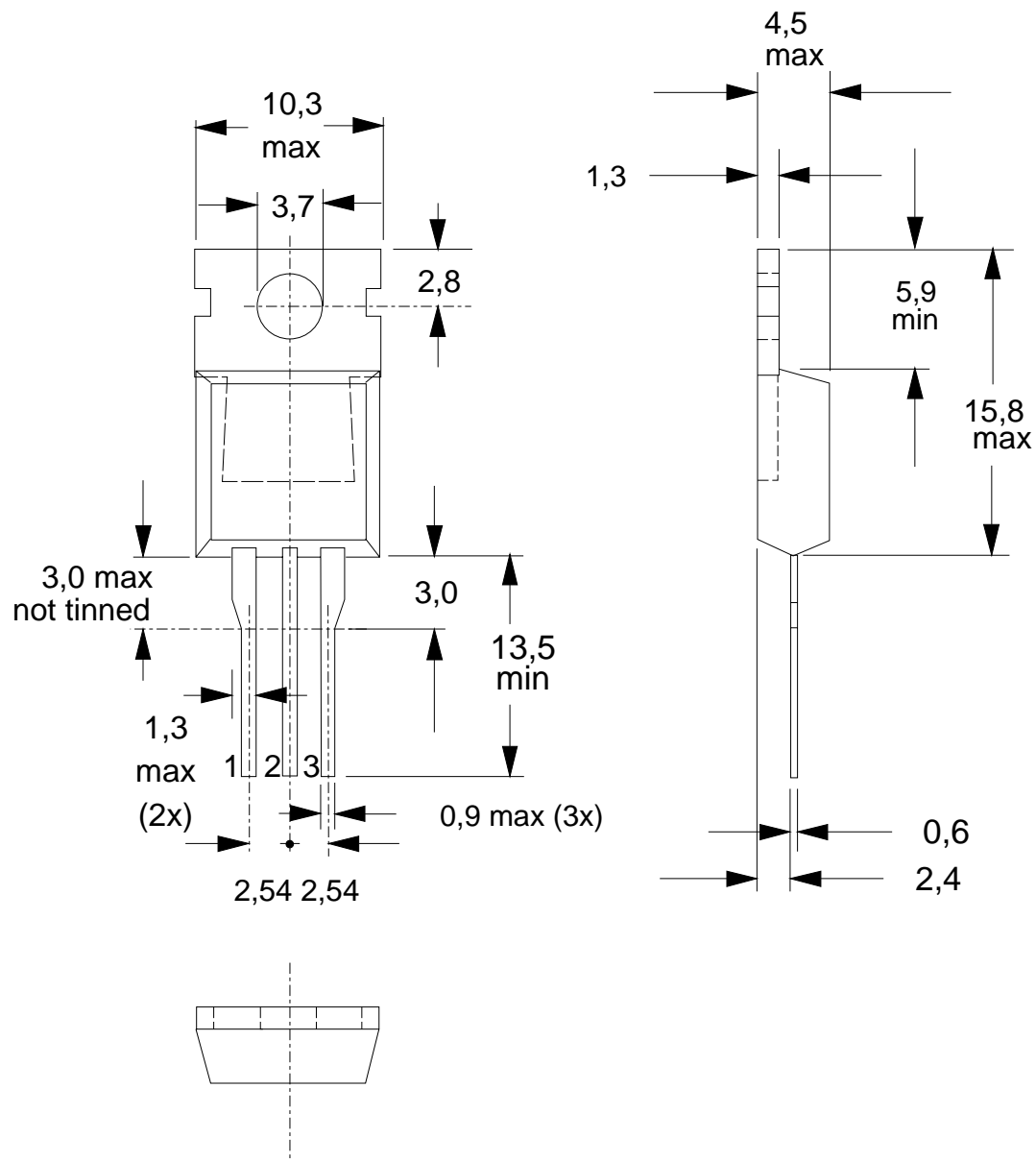


Fig.6. TO220AB; pin 2 connected to mounting base.

#### Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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### DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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